



Supporting Information

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Unlocking Deep and Fast Potassium-Ion Storage
through Phosphorus Heterostructure

*Xiaoju Zhao, Shitao Geng, Tong Zhou, Yan Wang,
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**Unlocking deep and fast potassium-ion storage through phosphorus
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Electrochemical measurements

GITT profiles were measured intermittently with pulse current of 100 mA g⁻¹ at discharge interval of 20 min and rest interval of 1 h. The diffusion coefficients were deduced from Fick's second law as follows^[1]:

$$D_K^+ = \frac{4}{\pi\tau} \left(\frac{m_B V_M}{M_B S} \right)^2 \left(\frac{\Delta E_s}{\Delta E_t} \right)^2$$

where D_K^+ is the K-ion diffusion coefficient, τ is the galvanostatic discharge time (s), m_B , M_B and V_M are the mass, molar mass and molar volume of the active material, respectively. V_M/M_B can be simplified as the density of active material. S is the surface area of the electrode, ΔE_s represents the voltage change at the steady state and ΔE_t represents the voltage change at galvanostatic discharge state.

The relationship between the current response and scan rate of CV curves was deduced based on following equation:

$$i = a v^b$$

where i and v represent current (mA) and scan rate (mV s⁻¹) respectively. a and b represent variable parameters. In this regard, b value reveals the contribution types of potassiation process. When b equals to 1.0, the redox reaction is mainly a surface capacitive process. When b equals to 0.5, the redox reaction is mainly a diffusive-controlled process. With the value of b between 0.5–1.0, both capacitive and diffusive behaviors exist, and their contribution can be quantitatively calculated based on the equation below:

$$i = i_{capacitive} + i_{diffusive} = k_1 v + k_2 v^{1/2}$$

where $k_1 v$ represents surface capacitive process, and $k_2 v^{1/2}$ represents diffusive-controlled process.

Computational details

All the spin theoretical simulations in our work were carried out on the Vienna ab initio Simulation Package (VASP) with Version 5.4.4.^[2,3] The Generalized gradient approximation (GGA) with the Perdew-Burke-Emzerhof (PBE)^[4] functional form was employed to evaluate the electron-electron exchange and correlation interactions, and the projector augmented-wave (PAW) methods^[5,6] were implanted to represent the core-electron (valence electron) interactions. Plane-Wave basis function was set with a kinetic cut-off energy of 550 eV. The ground-state atomic geometries were

optimized by relaxing the force below $0.02 \text{ eV}/\text{\AA}$ and the convergence criteria for energy was set with the value of $1.0 \times 10^{-5} \text{ eV}/\text{cell}$. Gaussian smearing and tetrahedron method with Blöchl corrections were employed for the stress/force relaxations and electronic structures, respectively. In order to better describe the interactions between molecules, van der Waal (vdW) interactions were included describing by zero damping DFT-D3 method of Grimme.^[7,8] To investigate K-ion adsorption and diffusion for BRPH structure, black phosphorus part was modeled using a 2×4 supercell with two phosphorene layers, while red phosphorus part was modeled using a zig-zag ladder structure (two chains with total 28 P atoms). To investigate K-ion adsorption and diffusion inside RP interlamination, structure model with four RP chains with total 56 P atoms was used. Vacuum layer of 25 \AA was set to avoid the interaction between neighboring cell in vertical direction. The Brillion zone was sampled using a $4 \times 6 \times 1$ Monkhorst–Pack grid with Gamma centered. The transition states during K diffusion pathways were evaluated using the Climbing-image nudged elastic band (CI-NEB) method^[9,10] with convergence criteria of force were below $0.05 \text{ eV}/\text{\AA}$.

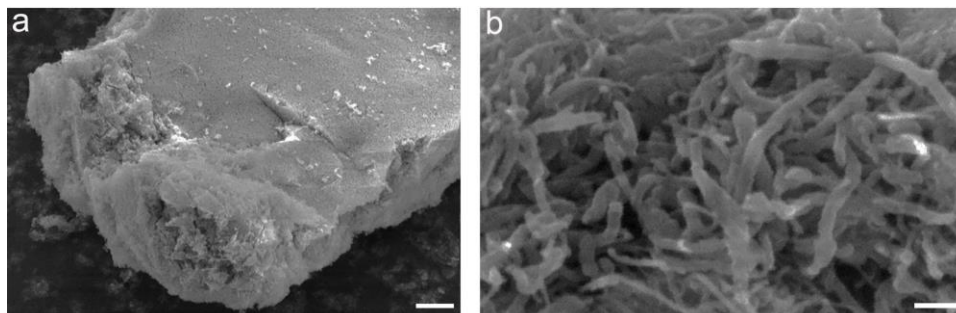


Figure S1. SEM images of the pretreated RP and RP@MWCNT, respectively. Scale bars, 1 μm (a) and 100 nm (b).

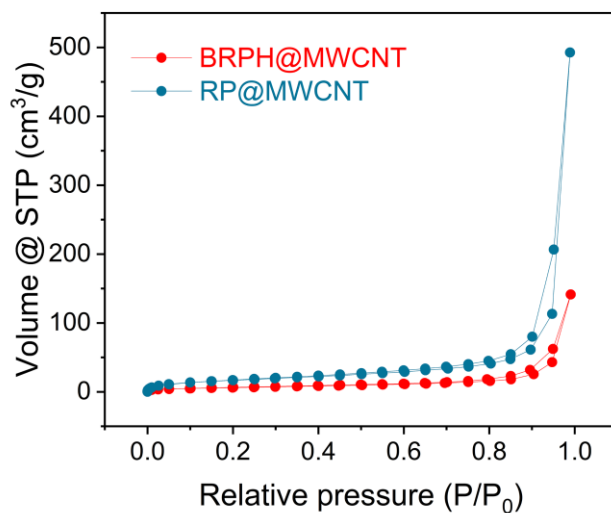


Figure S2. Nitrogen adsorption/desorption isotherms of BRPH@MWCNT and RP@MWCNT.

Based on the Brunauer-Emmett-Teller (BET) method, specific surface areas of BRPH@MWCNT and RP@MWCNT were 22.73 and 62.00 m² g⁻¹, respectively.

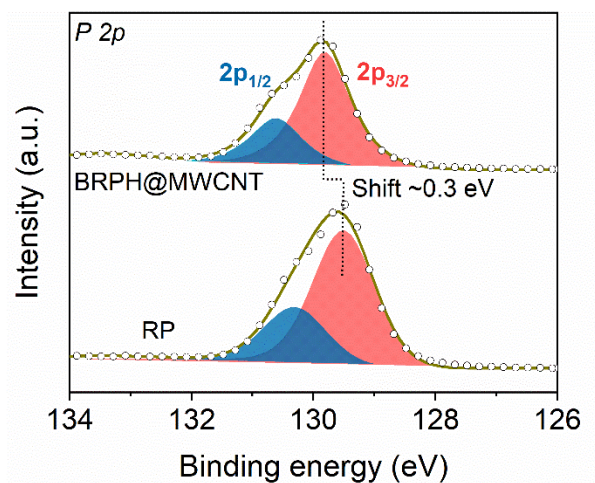


Figure S3. XPS profile of the RP and BRPH@MWCNT.

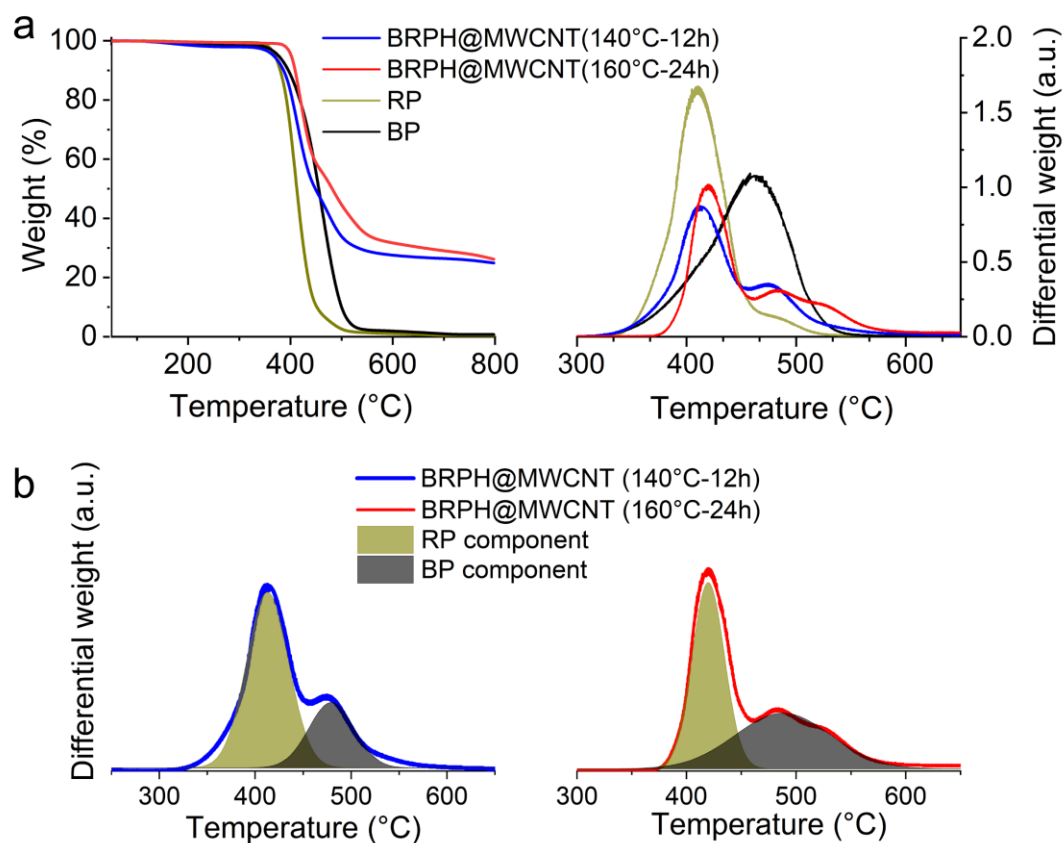


Figure S4. a, Normalized thermogravimetric (TG) analysis curves and corresponding differential thermogravimetric (-dTG) profiles of BRPH@MWCNT, RP and BP. **b**, the deconvoluted peaks of BRPH@MWCNT materials with different BP/RP ratios.

The RP counterpart in **Figure S4** was hydrothermally treated in DI water at 200 °C and BP was synthesized through the ethane diamine (EDA) solvothermal treatment of RP at 200 °C for 48 h. Two representative samples of BRPH@MWCNT were obtained based on the same EDA solvothermal procedure at **Experimental section** except for the variations of temperature and time. For instance, the BRPH@MWCNT obtained at 140 °C and 12 h, named as BRPH@MWCNT (140 °C–12 h), showed a BP/RP ratio of 0.4 based on the deconvoluted peaks in **Figure S4b**, as a comparison, the BRPH@MWCNT obtained at 160 °C and 24 h, named as BRPH@MWCNT (160 °C–24 h), showed a BP/RP ratio of 0.9 (**Figure S4b**). Thus, both temperature and time variations in the EDA-solvothermal process contributed to the BP/RP proportion of the as-synthesized heterostructure material.

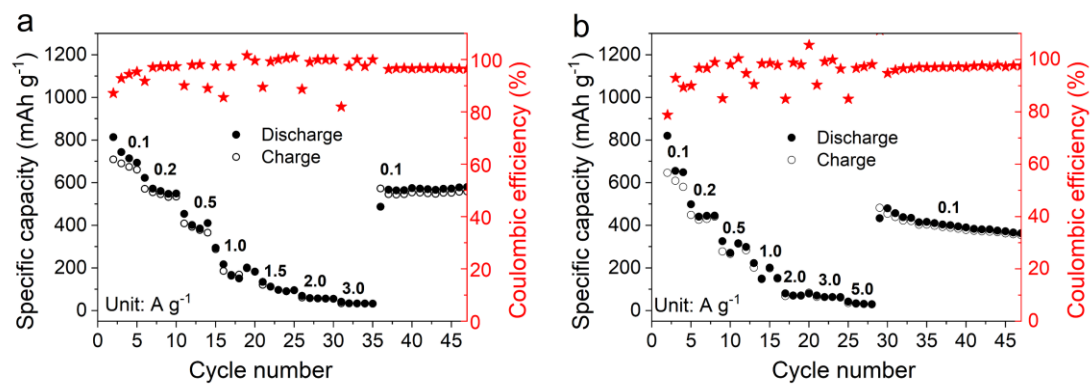


Figure S5. Rate performances of counterparts with different BP/RP ratios. **a**, BRPH@MWCNT (140 °C–12 h), BP/RP ratio: 0.4. **b**, BP@MWCNT (200 °C–48 h), BP/RP ratio: 1.0.

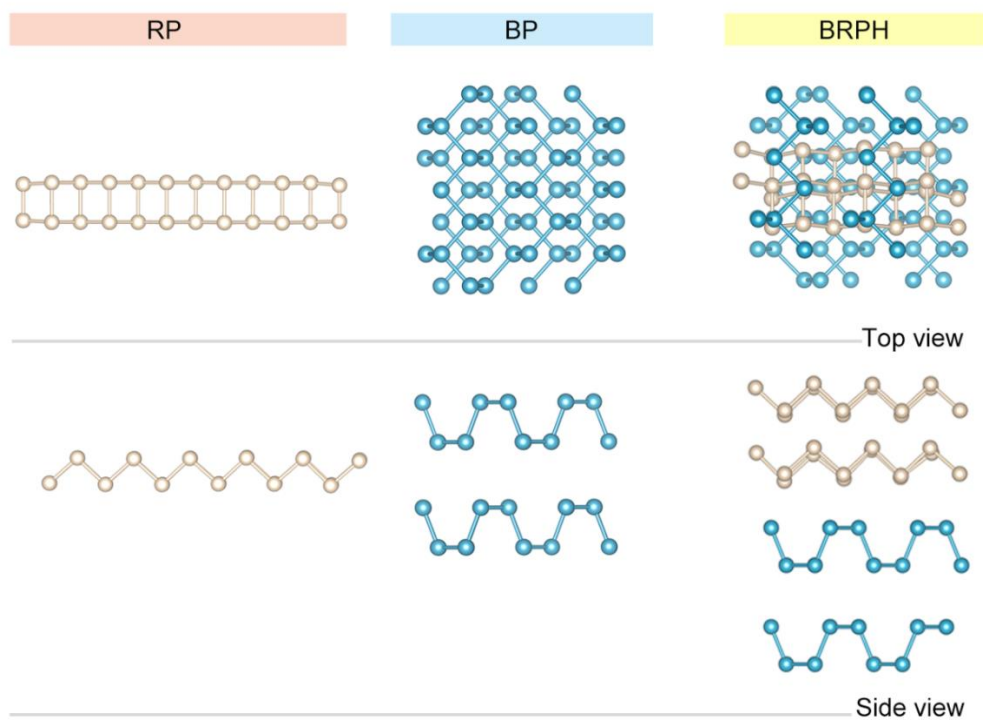


Figure S6. Structure models of RP, BP and BRPH from top and side views for DFT calculations.

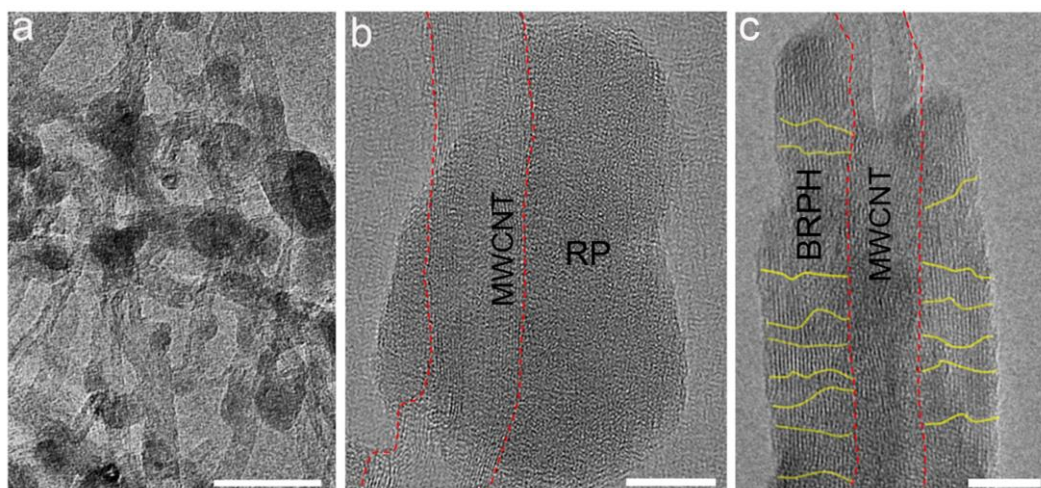


Figure S7. TEM images of the RP@MWCNT and BRPH@MWCNT. **a, b**, TEM images of RP@MWCNT. **c, d**, TEM image of BRPH@MWCNT. Scale bars are 50, 10 and 10 nm for **a, b** and **c**, respectively. The red and yellow lines represent MWCNT/BRPH interface and BP/RP heterointerface, respectively.

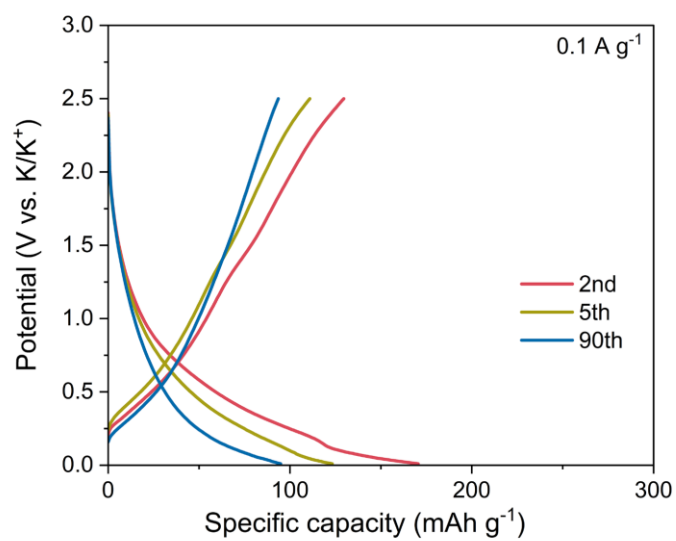


Figure S8. Galvanostatic discharge-charge curves of K metal/MWCNT half cell. The electrolyte is 4 M KFSI and 1 M KTFSI in EC/DMC (1:1 by volume). Current density, 0.1 A g⁻¹.

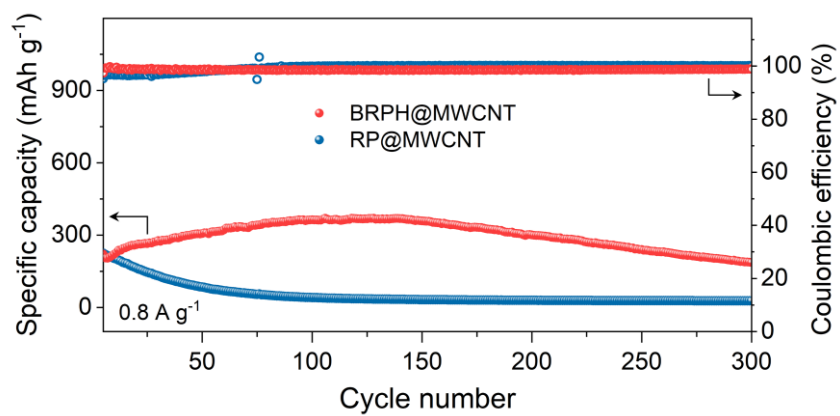


Figure S9. Cycling performance of RP@MWCNT and BRPH@MWCNT at the current density of 0.8 A g⁻¹.

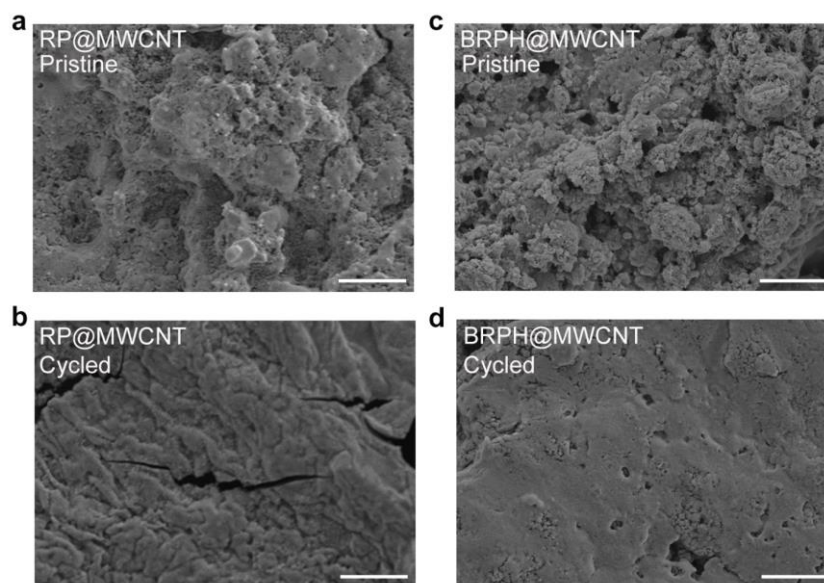


Figure S10. **a, b**, SEM images of RP@MWCNT anode before and after cycling for 20 cycles, respectively. **c, d**, SEM images of BRPH@MWCNT anode before and after cycling for 20 cycles, respectively. Scale bars, 2 μm .

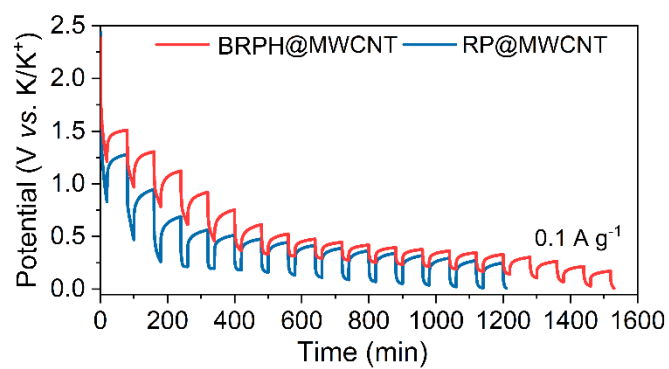


Figure S11. Galvanostatic intermittent titration (GITT) profiles of BRPH@MWCNT and RP@MWCNT anodes. Current density, 0.1 A g⁻¹.

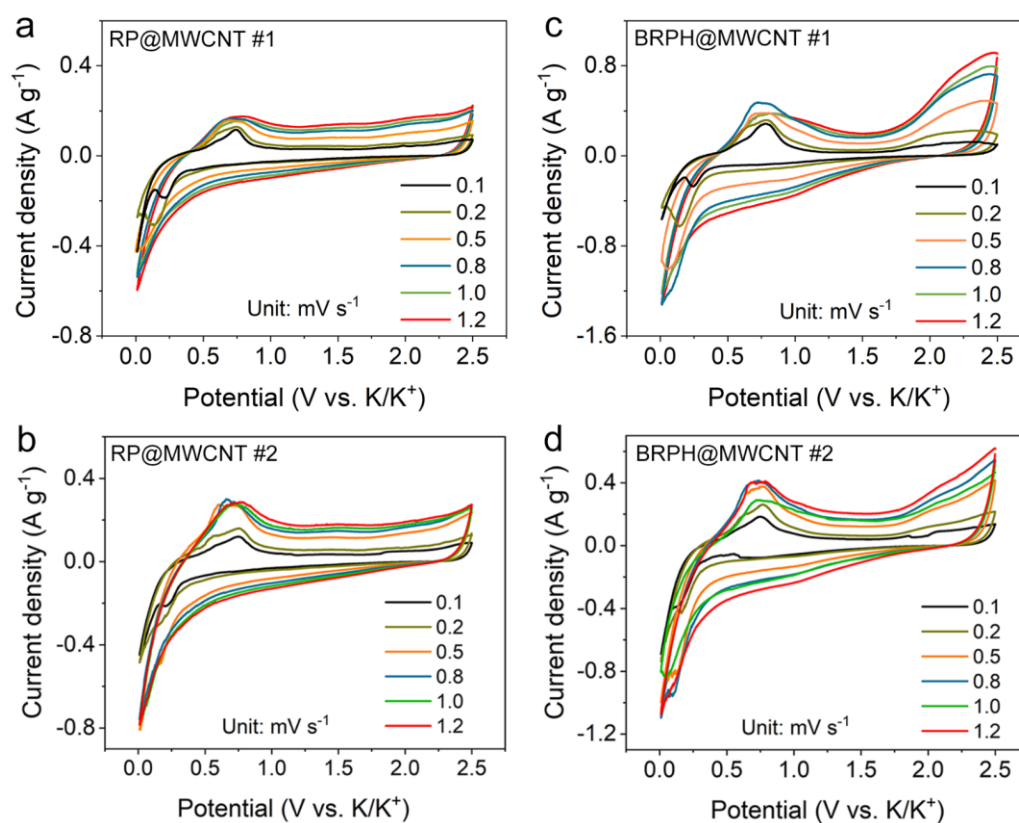


Figure S12. a, b, Parallel CV measurements of RP@MWCNT at various scan rates from 0.1 to 1.2 mV s⁻¹. c, d, Parallel CV measurements of BRPH@MWCNT at various scan rates from 0.1 to 1.2 mV s⁻¹.

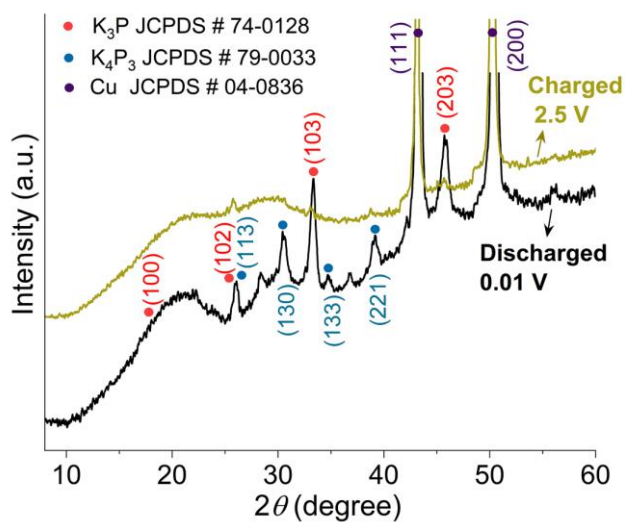


Figure S13. *Ex situ* XRD patterns of BRPH@MWCNT anodes at fully potassiated and depotassiated states.

We showed the prominent K_3P and K_4P_3 peaks in fully-discharged BRPH@MWCNT, and these peaks disappeared when further charged to 2.5 V vs. K/K^+ .

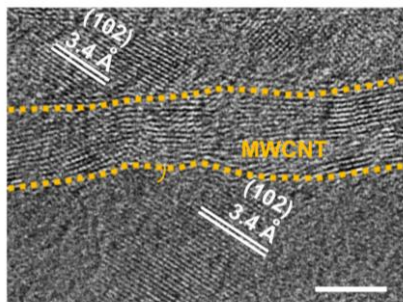


Figure S14. HRTEM analysis of BRPH@MWCNT after potassiated to 0.01 V vs. K/K⁺. Scale bar, 5 nm.

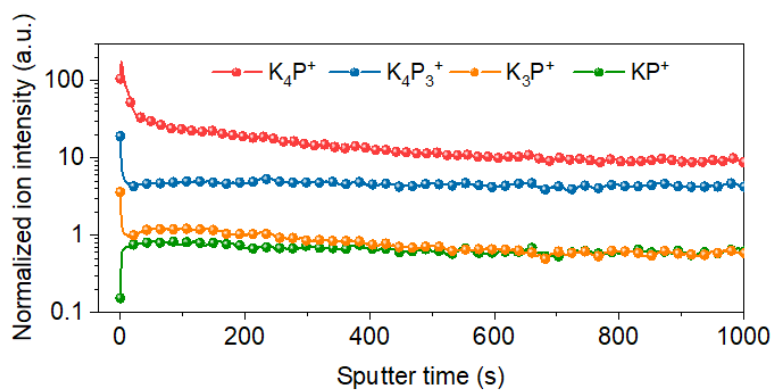


Figure S15. The normalized ion intensity of the four ion fragments (K_4P^+ , $K_4P_3^+$, K_3P^+ and KP^+) as a function of sputter time of the BRPH@MWCNT anode after potassiation.

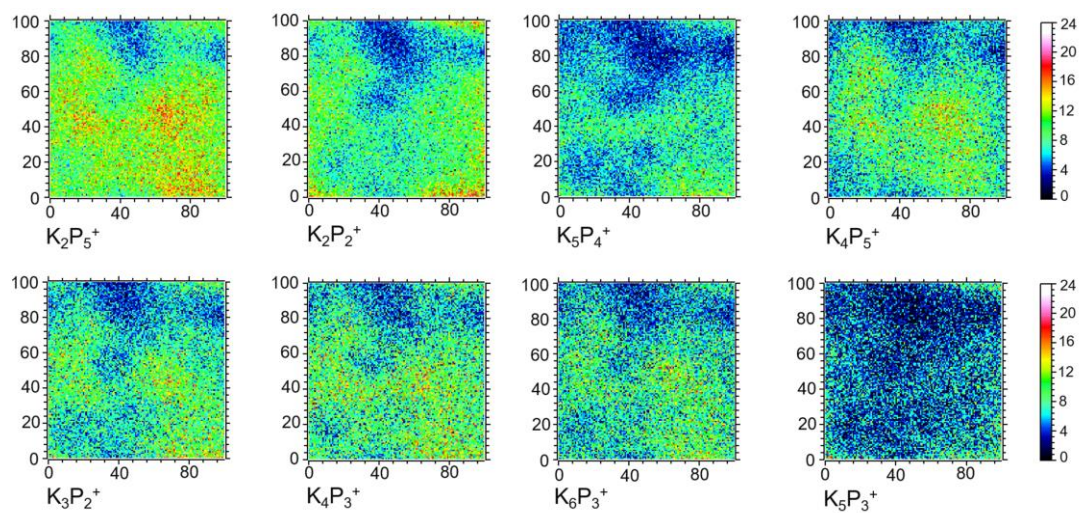


Figure S16. Intensity distributions of the main ion fragments ($K_2P_5^+$, $K_2P_2^+$, $K_5P_4^+$, $K_4P_5^+$, $K_3P_2^+$, $K_4P_3^+$, $K_6P_3^+$ and $K_5P_3^+$) of the RP@MWCNT anode after full potassiation.

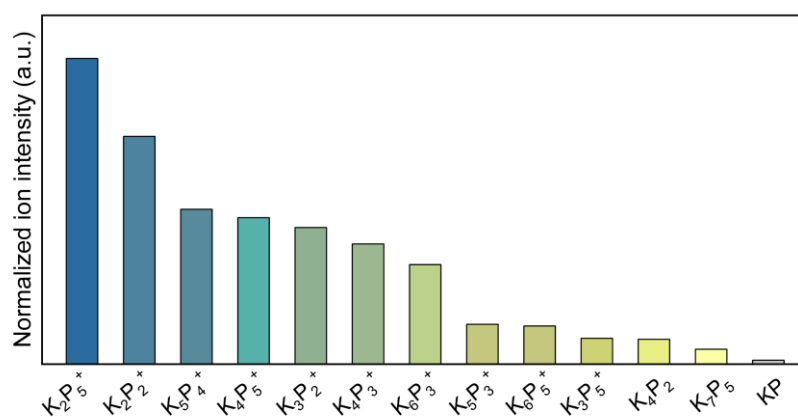


Figure S17. The normalized ion intensity of detectable ion fragments of the RP@MWCNT anode after full potassiation.

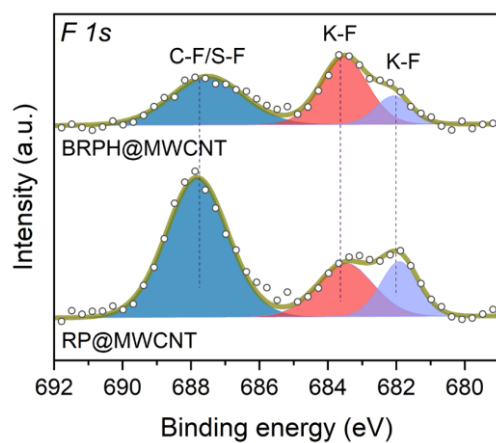


Figure S18. High-resolution XPS profile of F 1s of BRPH@MWCNT and RP@MWCNT after 20 cycles at a current density of 100 mA g^{-1} .

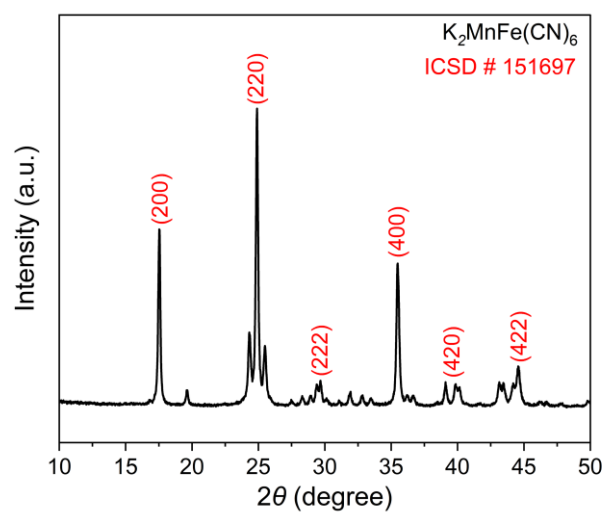


Figure S19. XRD patterns of the Prussian blue cathode.

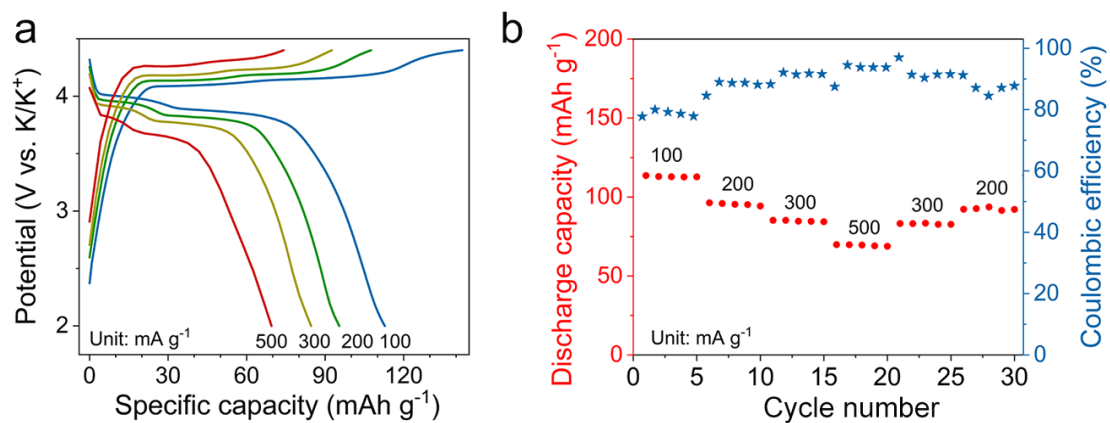


Figure S20. Rate performance of the K metal/Prussian blue half cell at various current densities from 100 to 500 mA g⁻¹.

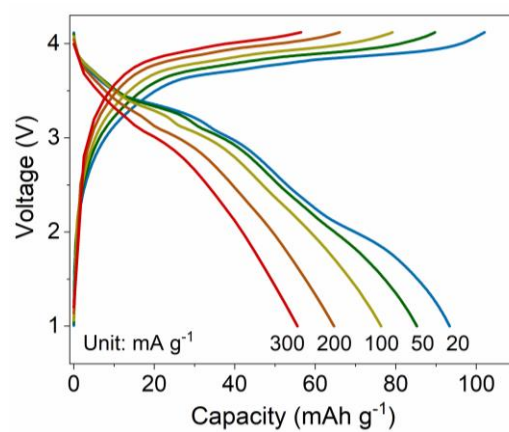


Figure S21. Rate performance of BRPH@MWCNT/Prussian blue full cell from 20 to 300 mA g⁻¹ with an N/P ratio of 1.4:1.

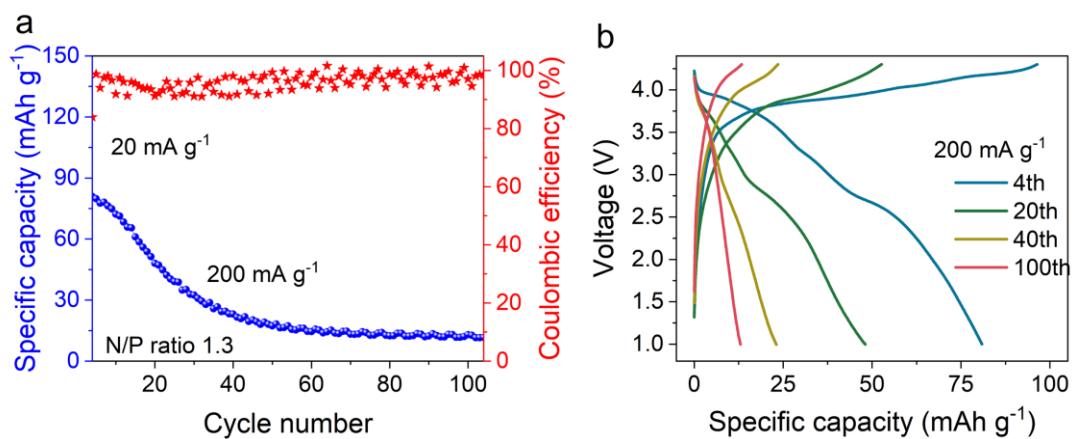


Figure S22. Cycling performance (a) and corresponding charge/discharge curves (b) of RP@MWCNT/Prussian blue full cell at 200 mA g⁻¹ with the optimized N/P ratio of 1.3:1. Current density, 200 mA g⁻¹. The cell was initially charge/discharged at 20 mA g⁻¹ for 3 cycles for stable SEI formation.

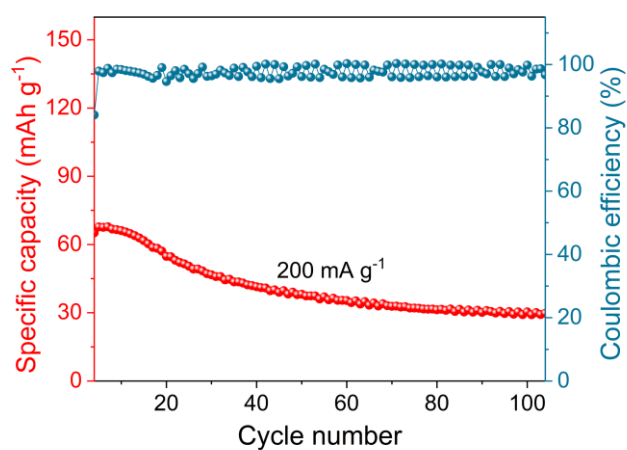


Figure S23. Cycling performance of the BRPH@MWCNT/Prussian blue full cell with a N/P ratio of 1.1. Current density, 200 mA g⁻¹. The cell was initially charge/discharged at 20 mA g⁻¹ for 3 cycles for stable SEI formation.

Table S1. Comparison on the main parameters of our BRPH@MWCNT and representative elemental P-based anode materials with high P contents .

Anodes with high P contents	P percentage (wt%)	Maximal specific capacity (mAh g ⁻¹)	Final potassiation product	Ref.
RP@N-PHCNFs	66	700 at 0.1 A g ⁻¹	K ₄ P ₃	[11]
P/C composite	65.4	739 at 0.2 A g ⁻¹	K ₄ P ₃	[1]
P@hollow C	75	841 at 0.05 A g ⁻¹	K ₄ P ₃	[12]
P@carbon nanosheet	63.9	715 at 0.1 A g ⁻¹	KP	[13]
BP/G	80	668 at 0.05 A g ⁻¹	K ₄ P ₃	[14]
P-rGO	31.5	418 at 0.1 A g ⁻¹	KP	[15]
RP@S-N-CNFs	59.2	524 at 0.1 A g ⁻¹	KP	[16]
BRPH@MWCNT	73.8	923 at 0.05 A g ⁻¹	K ₃ P	This work

Table S2. Charge transfer resistance (R_{ct}) of K metal/BRPH@MWCNT and K metal/RP@MWCNT half cells during the potassiation process. Both cells were cycled at 0.1 A g⁻¹ after 20 cycles and stopped at fully charged state prior to EIS measurement.

Voltage (V vs. K/K ⁺)	R_{ct} of BRPH@MWCNT (Ω)	R_{ct} of RP@MWCNT (Ω)
2.5	599.9	1410
1.0	598.9	1371
0.5	858.8	1204
0.4	983.7	1404
0.2	1059	2777
0.1	994.1	2830
0.01	981	7458

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